

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

CBR6M-L010M SERIES

GLASS PASSIVATED JUNCTION
SILICON BRIDGE RECTIFIER
6.0 AMP, 100 THRU 1000 VOLTS

CASE DMM

DESCRIPTION

The CENTRAL SEMICONDUCTOR CBR6M-L010M series types are silicon single phase full wave bridge rectifiers designed for general purpose, high current applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**

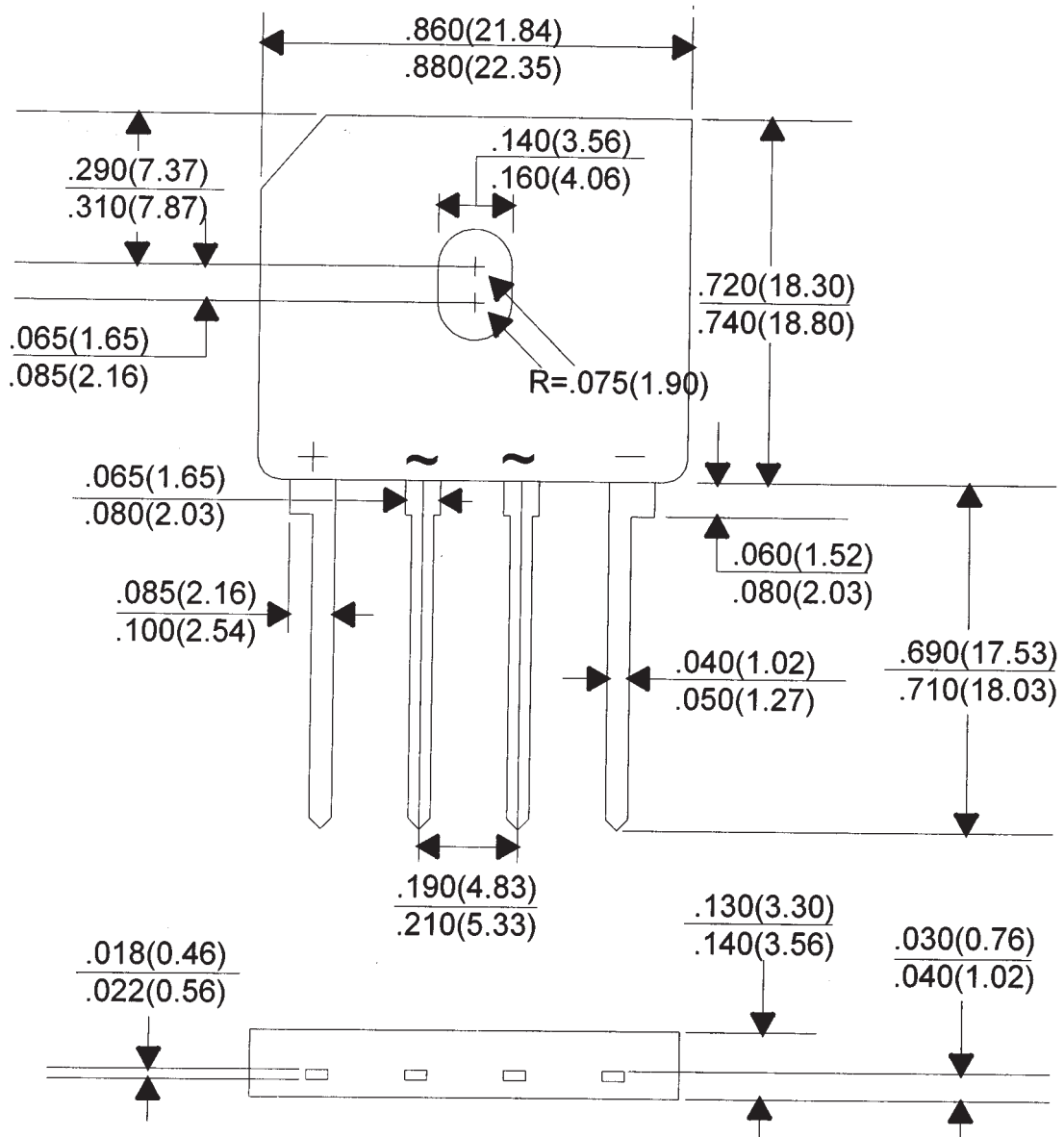
MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	CBR6M -L010M	CBR6M -L020M	CBR6M -L040M	CBR6M -L060M	CBR6M -L080M	CBR6M -L100M	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current ($T_C=100^\circ\text{C}$)	I_O				6.0			A
Peak Forward Surge Current	I_{FSM}				175			A
Operating and Storage Junction Temperature	T_J, T_{stg}				-65 to +150			$^\circ\text{C}$
Thermal Resistance	Θ_{JC}				3.1			$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R = \text{Rated } V_{RRM}$			5.0	μA
I_R	$V_R = \text{Rated } V_{RRM}, T_C = 100^\circ\text{C}$			500	μA
V_F	$I_F = 6.0\text{A}$			1.0	V
C_J	$V_R = 4.0\text{V}, f = 1.0\text{MHz}$		260		pF

CASE DMM - MECHANICAL OUTLINE



All Dimensions in Inches (mm).